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December 2015

FDP075N15A / FDB075N15A

N-Channel PowerTrench® MOSFET

150 V, 130 A, 7.5 mΩ

Features

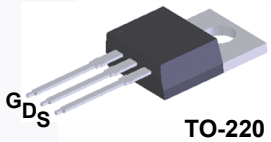
- $R_{DS(on)}$ = 6.25 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 100 A
- Fast Switching
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

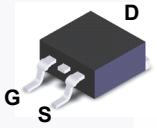
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

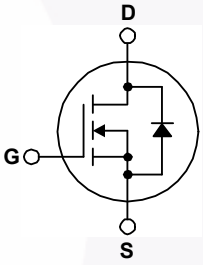
- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter



TO-220



D²-PAK



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDP075N15A_F102 FDB075N15A	Unit
V_{DSS}	Drain to Source Voltage		150	V
V_{GSS}	Gate to Source Voltage	- DC	±20	V
		- AC (f > 1 Hz)	±30	
I_D	Drain Current	- Continuous (T_C = 25°C)	130*	A
		- Continuous (T_C = 100°C)	92	
I_{DM}	Drain Current	- Pulsed (Note 1)	522	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	588	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P_D	Power Dissipation	(T_C = 25°C)	333	W
		- Derate Above 25°C	2.22	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

* Package limitation current is 120 A.

Thermal Characteristics

Symbol	Parameter	FDP075N15A_F102 FDB075N15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient, D2-PAK (1 in² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP075N15A_F102	FDP075N15A	TO-220	Tube	N/A	N/A	50 units
FDB075N15A	FDB075N15A	D^2-PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	150	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.1	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 120 V, T_C = 150°C	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 100 A	-	6.25	7.5	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 100 A	-	164	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz	-	5525	7350	pF
C_{oss}	Output Capacitance		-	516	685	pF
C_{rss}	Reverse Transfer Capacitance		-	21	-	pF
$C_{oss(er)}$	Energy Related Output Capacitance	V_{DS} = 75 V, V_{GS} = 0 V	-	909	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 75 V, I_D = 100 A, V_{GS} = 10 V (Note 4)	-	77	100	nC
Q_{gs}	Gate to Source Gate Charge		-	26	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	11	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	16	-	nC
ESR	Equivalent Series Resistance(G-S)	f = 1 MHz	-	2.29	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75 V, I_D = 100 A, V_{GS} = 10 V, R_G = 4.7 Ω (Note 4)	-	28	66	ns
t_r	Turn-On Rise Time		-	37	84	ns
$t_{d(off)}$	Turn-Off Delay Time		-	62	134	ns
t_f	Turn-Off Fall Time		-	21	52	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	130*	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	520	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 100 A	-	-	1.25	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, V_{DD} = 75 V, I_{SD} = 100 A, dI_F/dt = 100 A/μs	-	97	-	ns
Q_{rr}	Reverse Recovery Charge		-	264	-	nC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. Starting T_J = 25°C, L = 3 mH, I_{AS} = 19.8 A.
3. I_{SD} ≤ 100 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

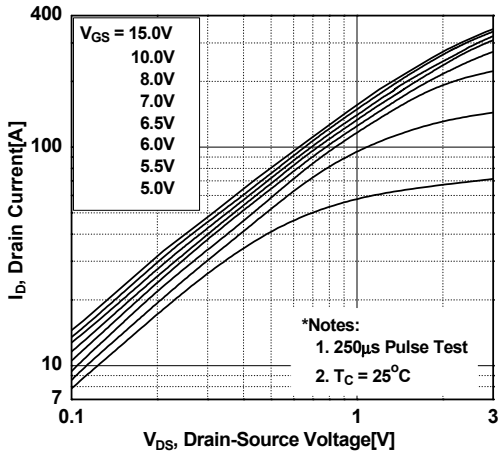


Figure 2. Transfer Characteristics

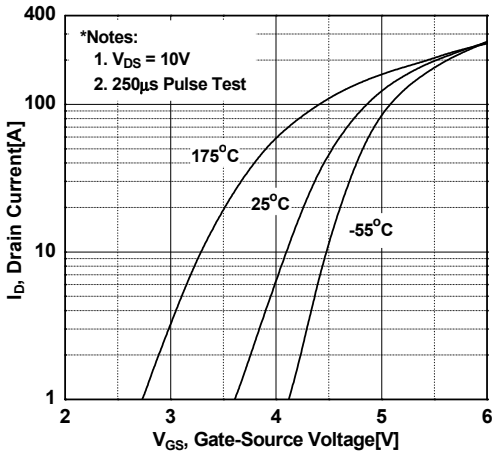


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

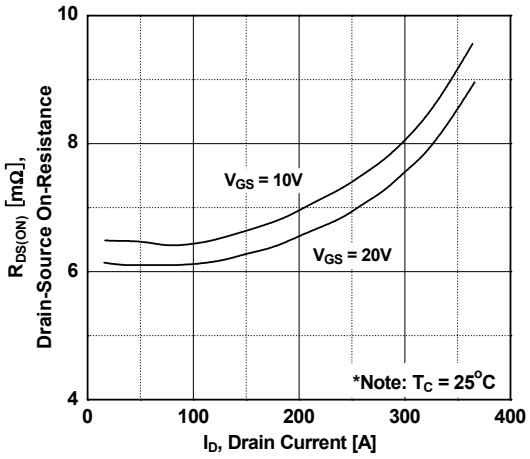


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

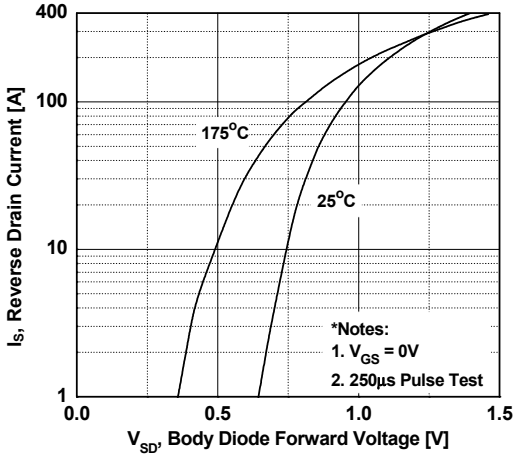


Figure 5. Capacitance Characteristics

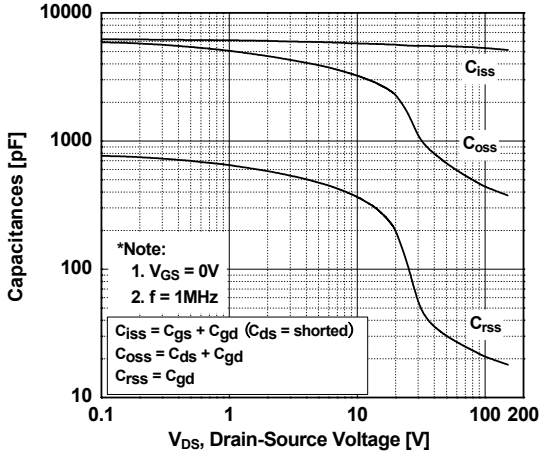
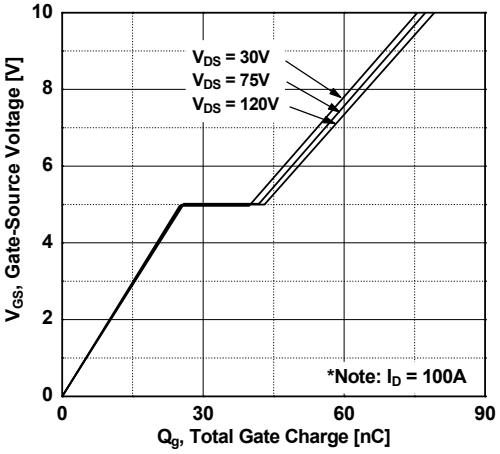


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

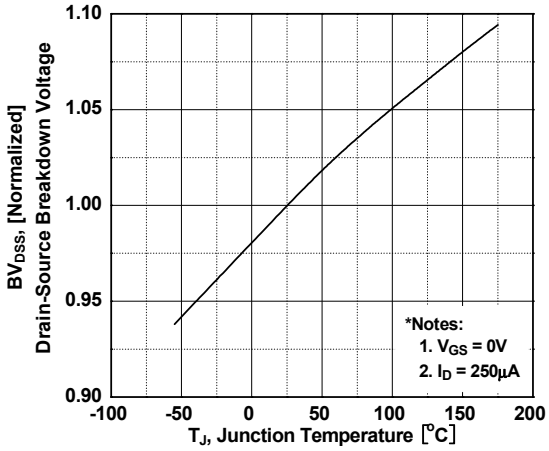


Figure 8. On-Resistance Variation vs. Temperature

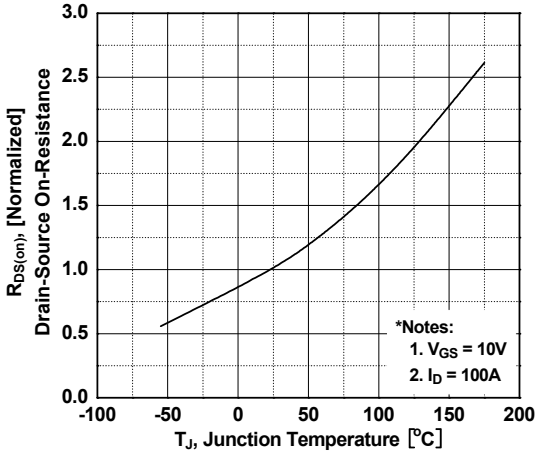


Figure 9. Maximum Safe Operating Area

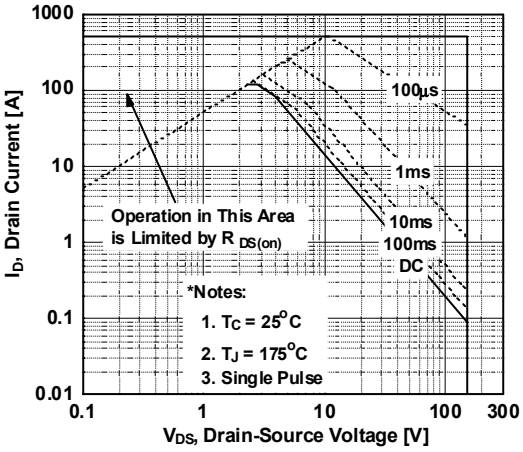


Figure 10. Maximum Drain Current vs. Case Temperature

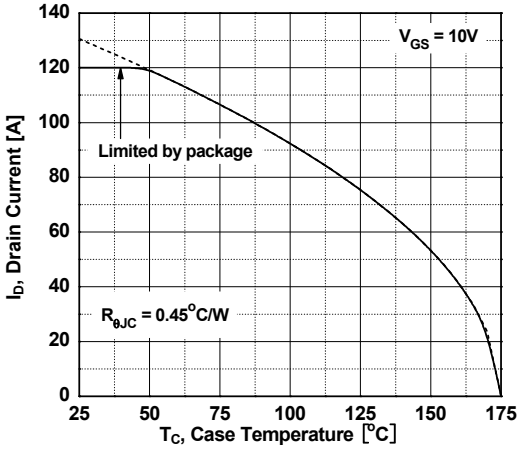


Figure 11. Eoss vs. Drain to Source Voltage

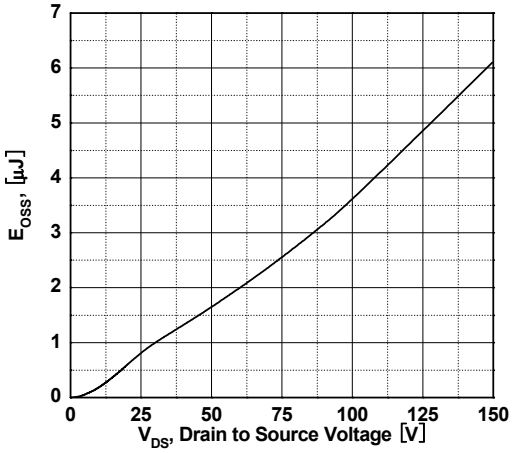
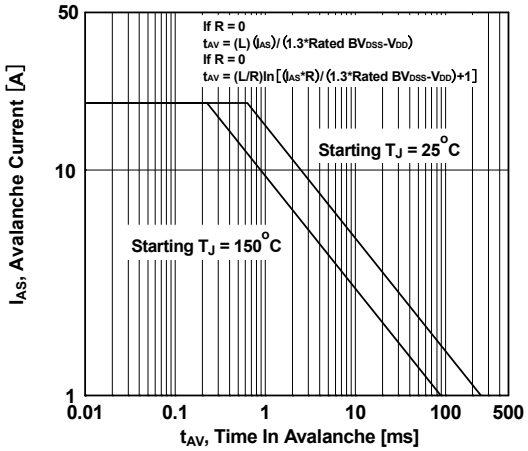
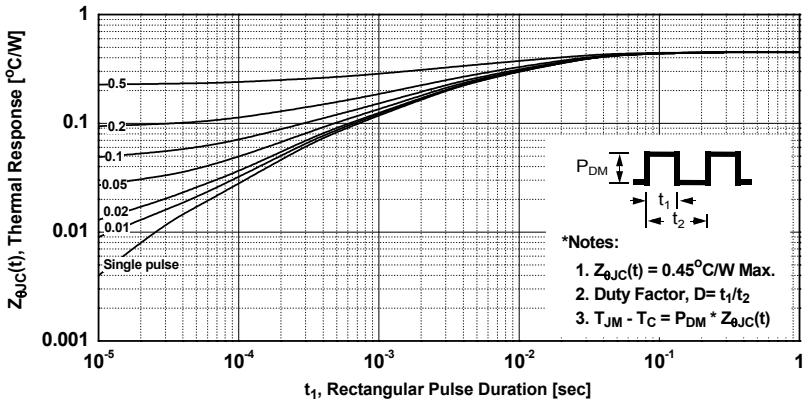


Figure 12. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve



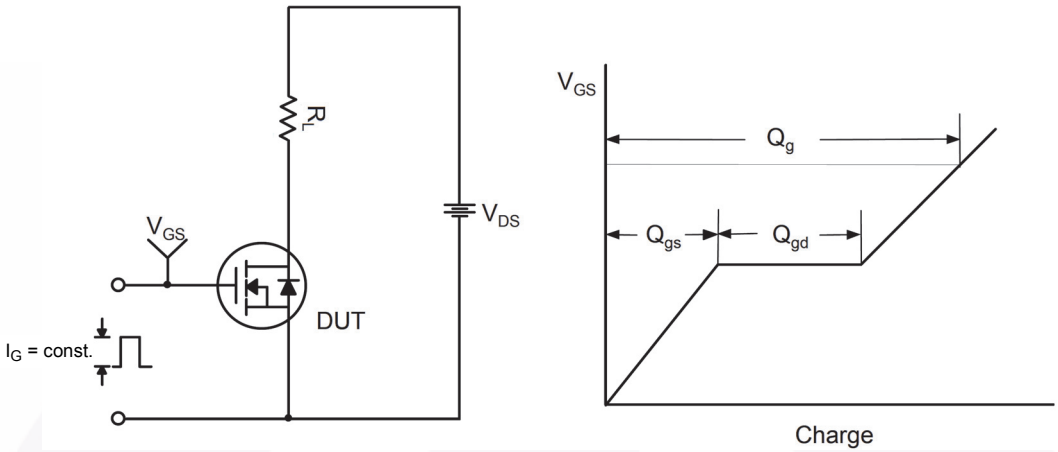


Figure 14. Gate Charge Test Circuit & Waveform

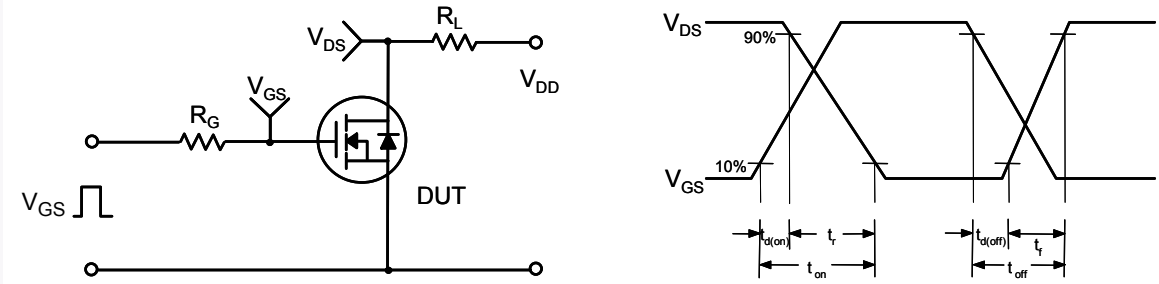


Figure 15. Resistive Switching Test Circuit & Waveforms

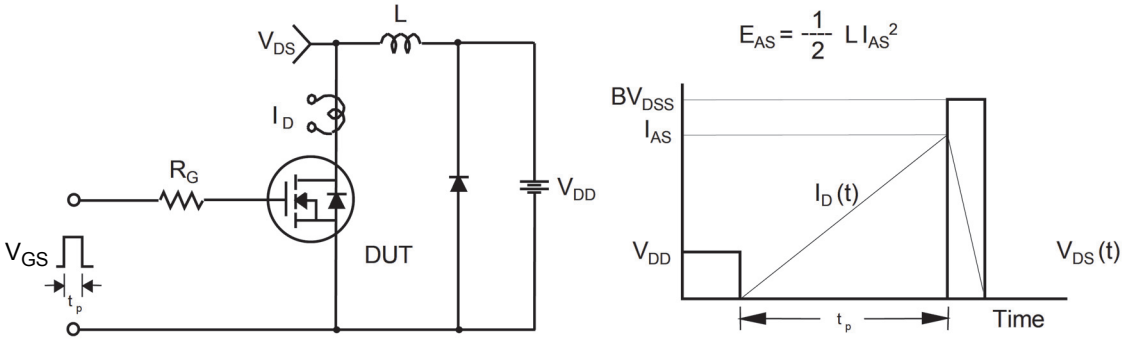


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

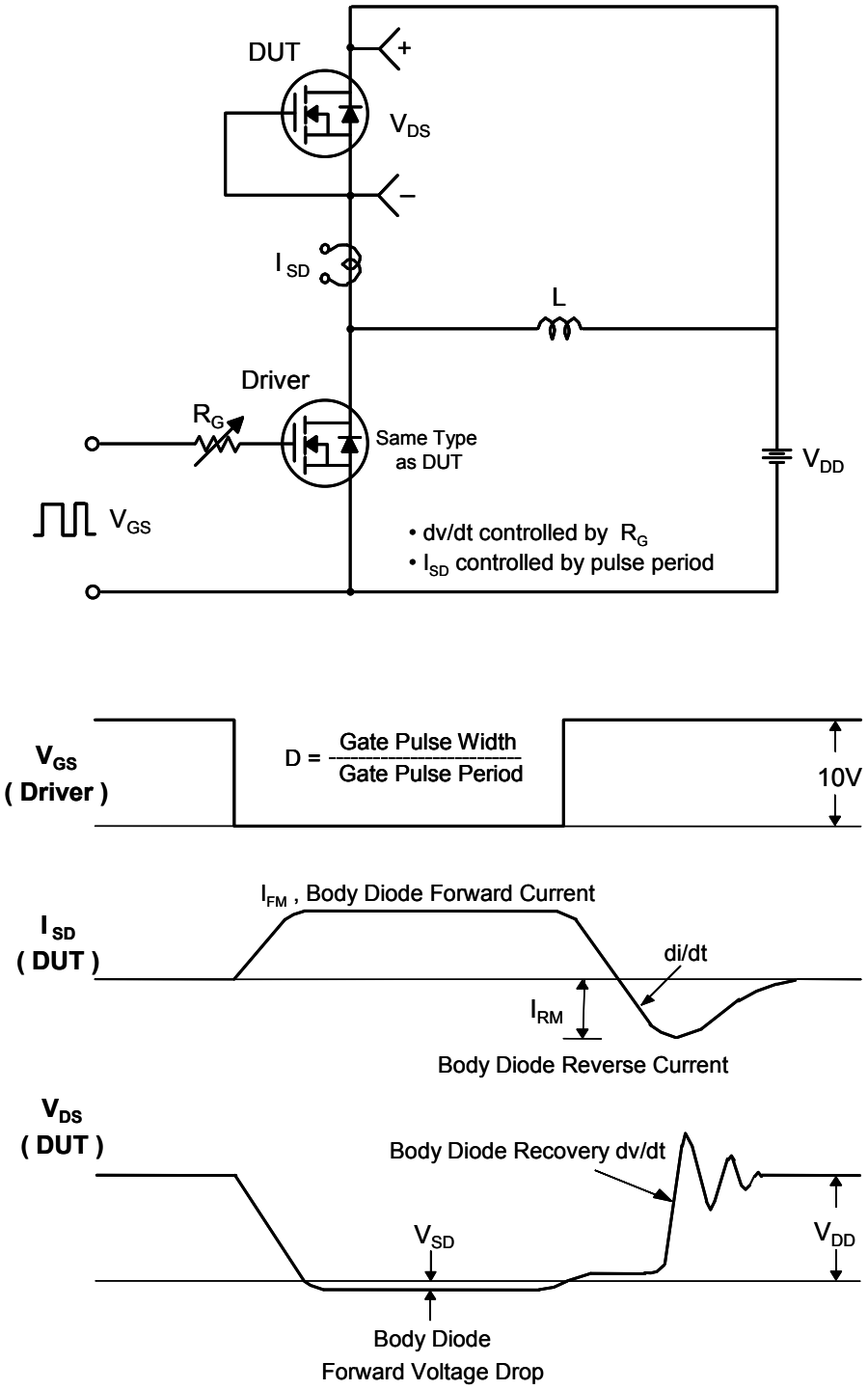
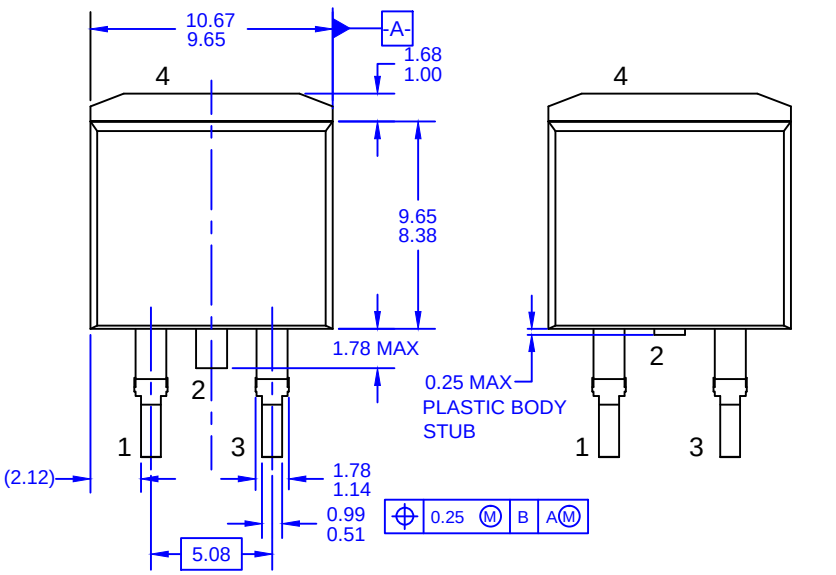
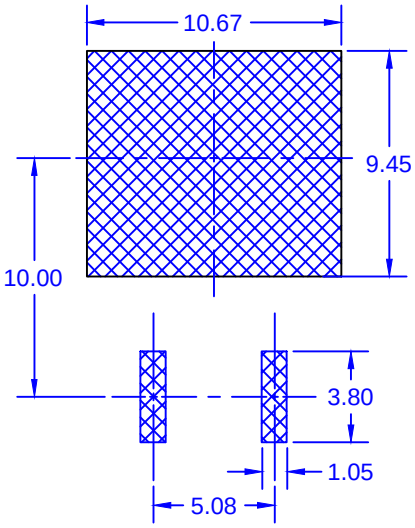


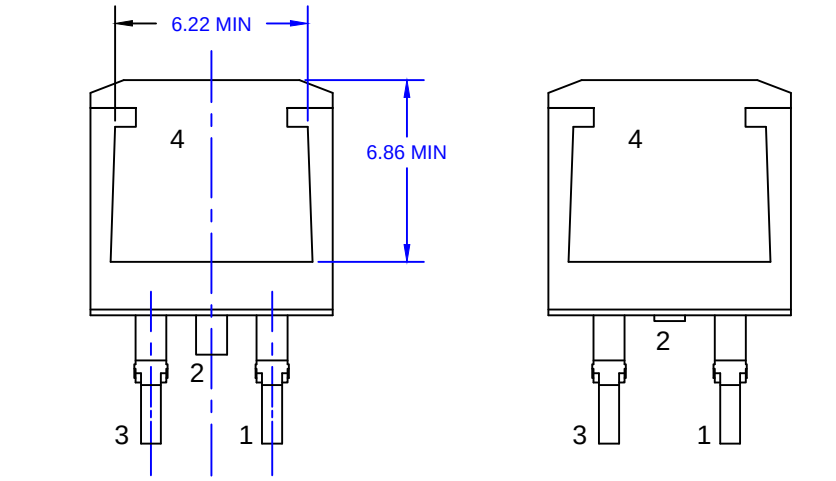
Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms



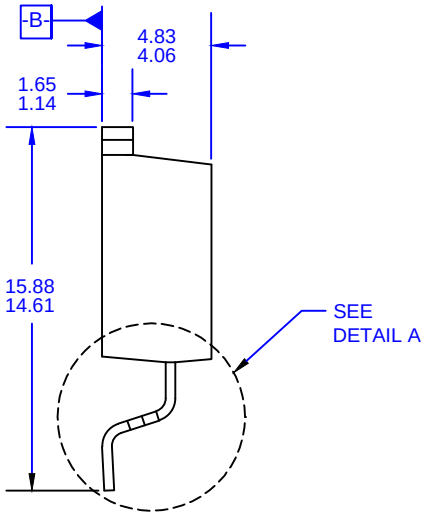
FRONT VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



LAND PATTERN RECOMMENDATION
UNLESS NOTED, ALL DIMS TYPICAL

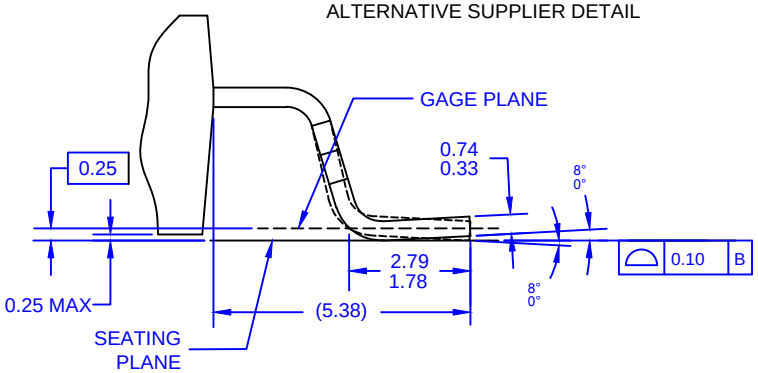


BACK VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



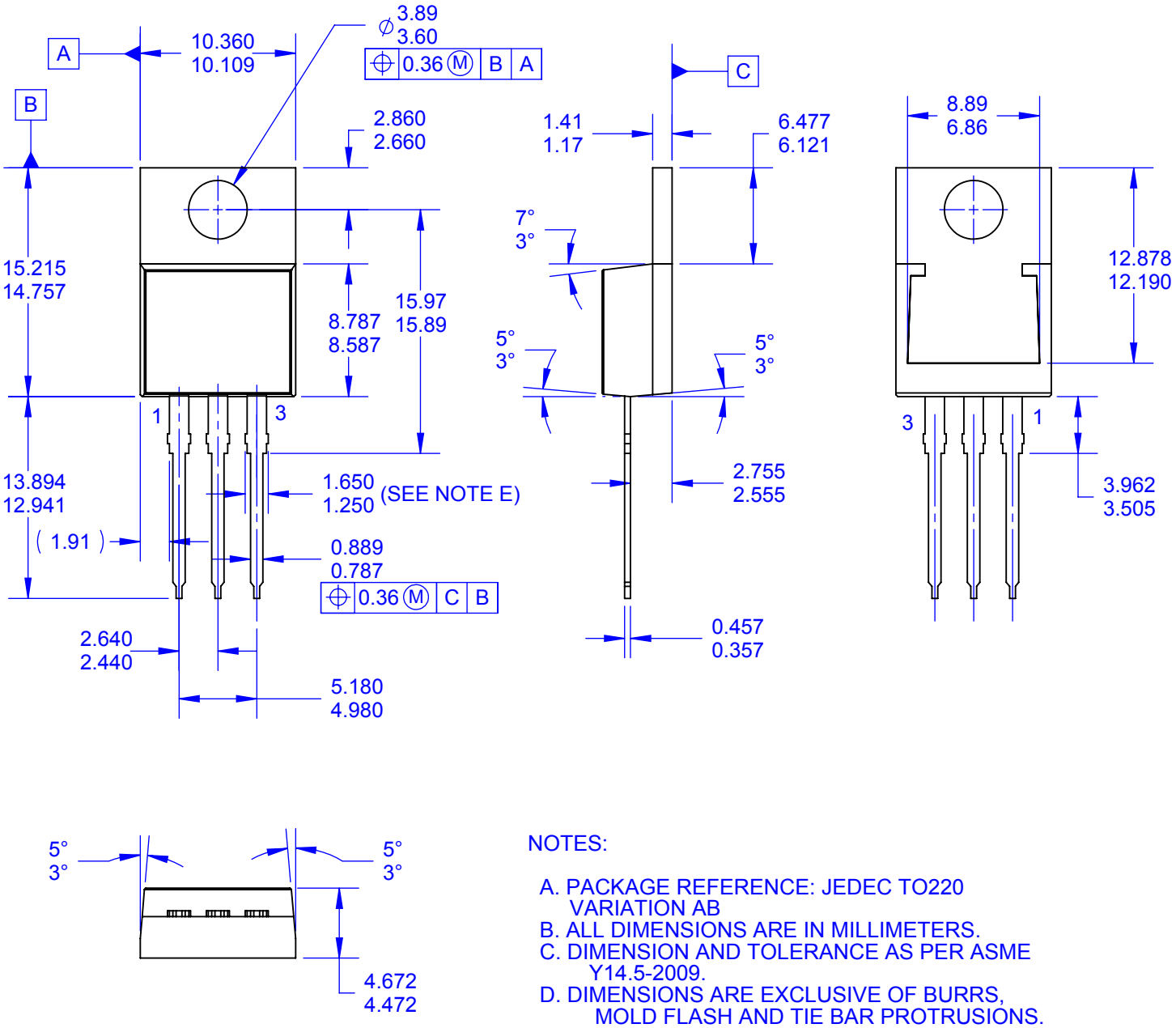
NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) REFERENCE JEDEC, TO-263, VARIATION AB.
C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
F) FILENAME: TO263A02REV8



DETAIL A, ROTATED 90°
SCALE: 2X

FAIRCHILD.



NOTES:

A. PACKAGE REFERENCE: JEDEC TO220 VARIATION AB
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. MAX WIDTH FOR F102 DEVICE = 1.35mm.
F. DRAWING FILE NAME: TO220T03REV4.
G. FAIRCHILD SEMICONDUCTOR.

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